

EAST: [10674612.asymmetrical cells.wsp:1]

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Pending

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L1: (811) (257/903).CCLS.

L2: (172673) (asymmetry asymmetric \$4)

L3: (481) 2 adj (memory cell)

L4: (889) 2 near (memory cell)

L5: (111) and 4

(1) 09/948877

(1736) "KONINKLUKE PHILIPS".as.

(1) 10/674612

(2481584) memory cell

(0) first adj 10/674612

(54988) first adj (memory cell)

(51109) second adj (memory cell)

(11150) third adj (memory cell)

(120890) symmetries

(120880) symmetry

(876781) symmetry symmetric \$4 mirror

(686846) (asymmetry asymmetric \$4 mirror)

(166869) (asymmetry asymmetric \$4)

(22251) (first adj (memory cell)) near9 (second adj (memory cell))

(84) ((first adj (memory cell)) near9 (second adj (memory cell)) near9 (symmetry sym

(3295) (second adj (memory cell)) near9 (third adj (memory cell))

(3) ((first adj (memory cell)) near9 (second adj (memory cell)) near9 (symmetry sym

BrowseQueuesClear

QbsUSPAT:US PG PUB; EPO: JPO: DERWENT: IBM: TDO

Default operator: OR

Plurals

Highlight all hit terms initially

1 and 4

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	#	→	Inventor	Document#	Issue	P	Title	Current	Current	CR	Retrieval	S	C	P	→	→	Image	Doc	P
1			Rockett, Leo	US 2002002	20020	1	High-performance high-density CMOS sram c	257/389	257/903			R	F	F	F	F	F	US 200200	F
2			Houston, The	US 2001005	20011	1	SRAM with write-back on read	257/390	257/903			R	F	F	F	F	F	US 200100	F
3			Naffziger, Sa	US 8363006	20020	1	Asymmetric RAM cell	365/154	257/903			R	F	F	F	F	F	US 836300	F
4			Park, Joon Yo	US 6303966	20011	3	SRAM cell having overlapping access transis	257/393	257/379			R	F	F	F	F	F	US 630396	F
5			Naffziger, Sa	US 6240009	20010	1	Asymmetric ram cell	365/154	257/903			R	F	F	F	F	F	US 624000	F
6			Kim, Dong Su	US 6028340	20000	1	Static random access memory cell having a f	257/388	257/379			R	F	F	F	F	F	US 602834	F
7			Lien, Chuen-D	US 5790452	19980	7	Memory cell having asymmetrical source/dra	365/154	257/393			R	F	F	F	F	F	US 579045	F
8			Orlowski, Ma	US 5587958	19981	1	High-performance thin-film transistor and SR	257/68	257/330			R	F	F	F	F	F	US 558795	F
9			Yang, Ming-T	US 5461251	19951	1	Symmetric SRAM cell with buried N+ local i	257/379	257/903			R	F	F	F	F	F	US 546125	F
10			Pfister, Jam	US 5458688	18951	1	Semiconductor memory cell and fabrication	257/69	257/377			R	F	F	F	F	F	US 545868	F

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30/10/04